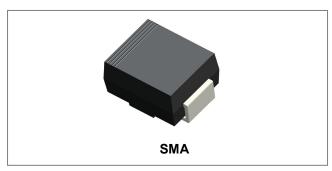


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10MQ200N SCHOTTKY RECTIFIER



Features

- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk Drives
- Switching power supply
- · Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$\begin{array}{c c} V_{RRM} & - \\ V_{RWM} & \\ V_{R} & \\ \hline \\ I_{F(AV)} & \text{rectangular wave form} \\ On PC \ \text{board } 9\text{mm}^2 \ \text{island} \\ \end{array}$		200	V
Average Forward Current			1	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse, T _C = 25 °C	20	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 1 A, Pulse, T _J = 25 °C	0.84	0.92	V
	V _{F2}	@ 1 A, Pulse, T _J = 125 °C	0.70	0.76	V
Reverse Current*	I _{R1}	$@V_R = Rated V_R, Pulse, T_J = 25 °C$	0.00001	0.5	mA
	I _{R2}	$@V_R = Rated V_R, Pulse, T_J = 125 °C$	0.01	1.0	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	17	20	PF
Typical Series Inductance	Ls	Ls Measured lead to lead 5 mm from package body		-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%



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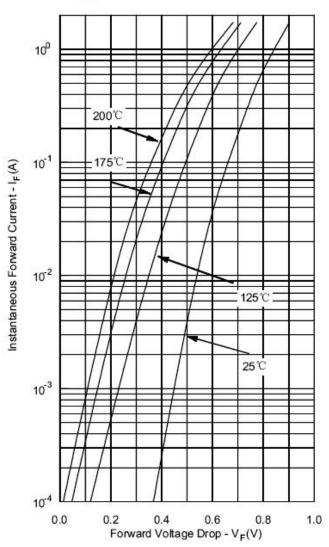


Thermal-Mechanical Specifications:

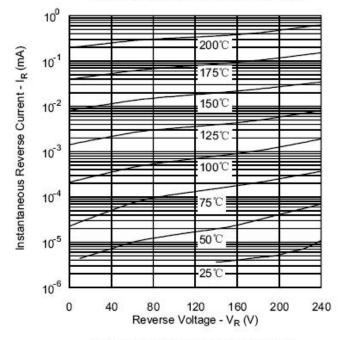
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	-	80	°C/W
Approximate Weight	wt	-	0.06	g
Case Style	SMA			

Ratings and Characteristics Curves

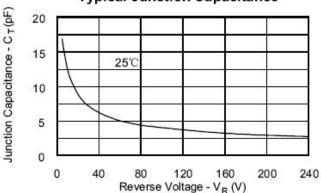
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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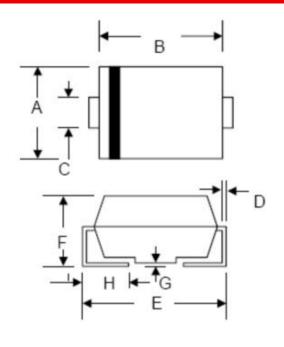


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Mechanical Dimensions SMA



CYMPOL	Millimeters		Inches	
SYMBOL	Min.	Max.	Min.	Max.
Α	2.40	2.84	0.094	0.112
В	3.99	4.75	0.157	0.187
С	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
Н	0.76	1.52	0.030	0.600

Ordering Information

Device		Package	Shipping		
	10MQ200N	SMA (Pb-Free)	5000pcs / reel		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

SA1N XXXXXX

Where XXXXX is YYWWL

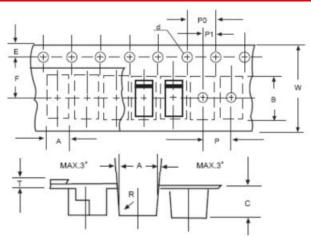
S = Device Type
A = Package Type
1 = Forward Current (1A)
N = Reverse Voltage (200V)
YY = Year
WW = Week

= Lot Number

Cautions: Molding resin

Epoxv resin UL:94V-0

Carrier Tape & Reel Specification SMA



SYMBOL	Millimeters		
STWIBUL	Min.	Max.	
Α	2.97	3.17	
В	5.70	5.90	
C	2.32	2.52	
d	1.40	1.60	
Е	1.40	1.60	
F	5.60	5.70	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
Т	0.25	0.35	
W	11.80	12.20	

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10MQ200N



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